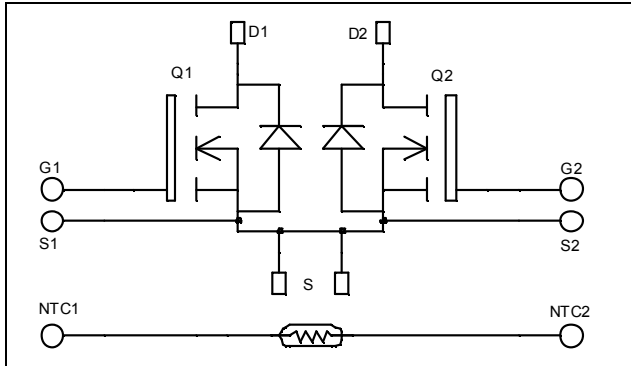


Dual Common Source MOSFET Power Module

$V_{DSS} = 1200V$

$R_{DSon} = 290m\Omega$ typ @ $T_j = 25^\circ C$

$I_D = 34A$ @ $T_c = 25^\circ C$

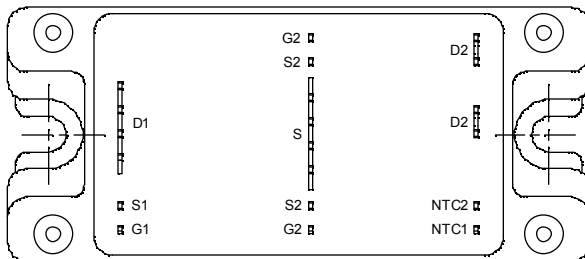


Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1200	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$ 34	A
		$T_c = 80^\circ C$ 25	
I_{DM}	Pulsed Drain current	136	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	348	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$ 780	W
I_{AR}	Avalanche current (repetitive and non repetitive)	22	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	3000	



CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1200V$			350	μA
		$V_{GS} = 0V, V_{DS} = 1000V$			1500	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 17A$		290	348	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5mA$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		10.3		nF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		1.54		
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		0.26		
Q_g	Total gate Charge	$V_{GS} = 10V$		374		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 600V$		48		
Q_{gd}	Gate – Drain Charge	$I_D = 34A$		240		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 800V$ $I_D = 34A$ $R_G = 2.5\Omega$		20		ns
T_r	Rise Time			15		
$T_{d(off)}$	Turn-off Delay Time			160		
T_f	Fall Time			45		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 800V$ $I_D = 34A, R_G = 2.5\Omega$		1980		μJ
E_{off}	Turn-off Switching Energy			1371		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 800V$ $I_D = 34A, R_G = 2.5\Omega$		3131		μJ
E_{off}	Turn-off Switching Energy			1714		

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_S	Continuous Source current (Body diode)	$T_c = 25^\circ\text{C}$			34	A
		$T_c = 80^\circ\text{C}$			25	
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -34A$			1.3	V
dv/dt	Peak Diode Recovery ❶				10	V/ns
t_{rr}	Reverse Recovery Time	$I_S = -34A; V_R = 600V$		1291		ns
Q_{rr}	Reverse Recovery Charge	$di/dt = 200A/\mu s$		58		μC

❶ dv/dt numbers reflect the limitations of the circuit rather than the device itself.

$I_S \leq -34A$ $di/dt \leq 700A/\mu s$ $V_R \leq V_{DSS}$ $T_j \leq 150^\circ\text{C}$

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance					0.16	°C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

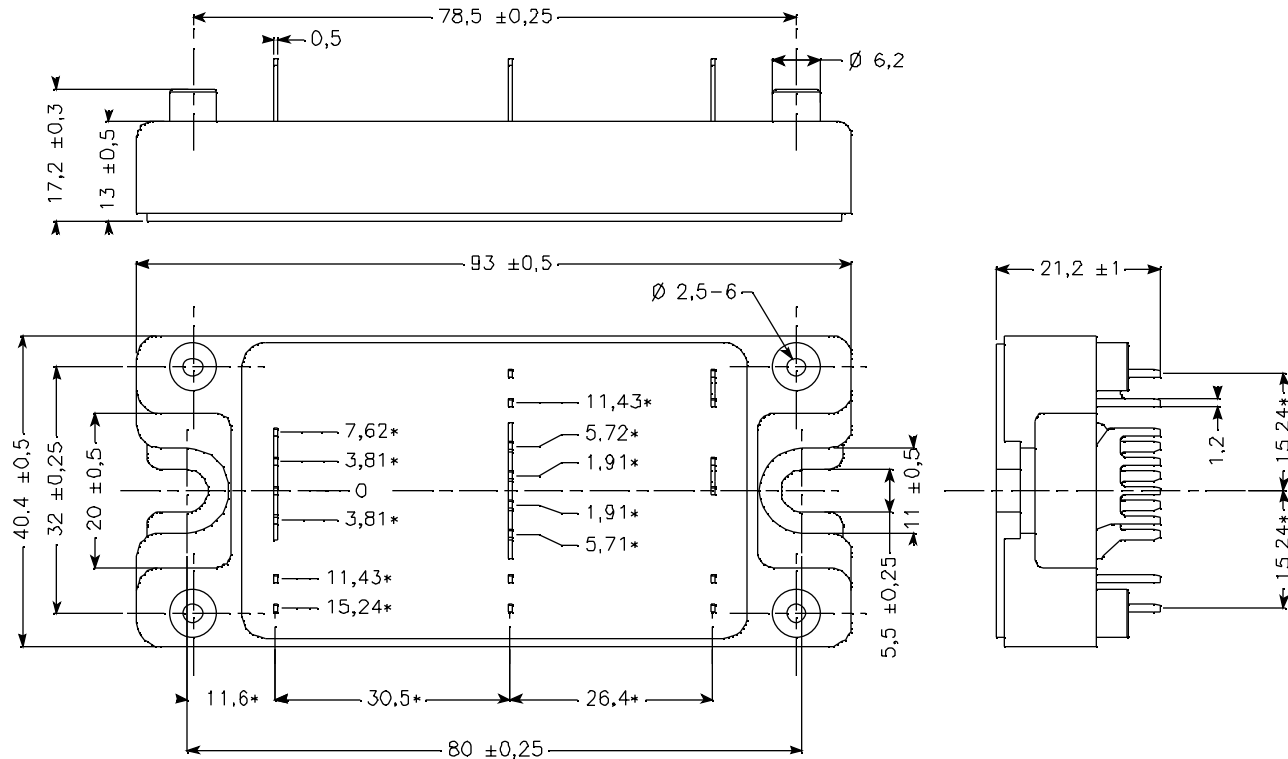
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T: Thermistor temperature
 R_T: Thermistor value at T

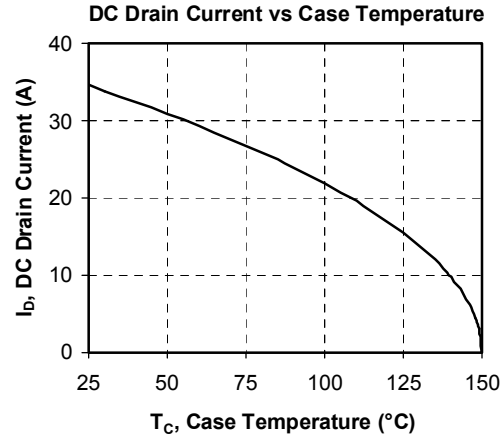
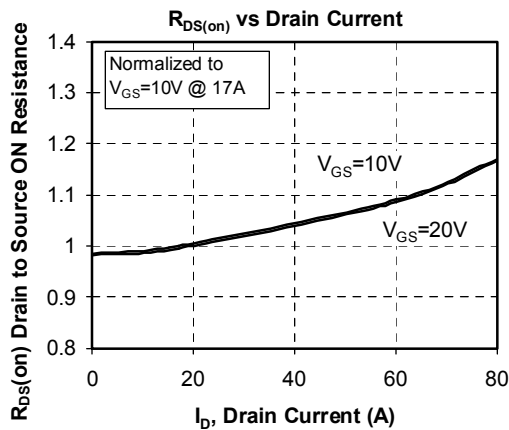
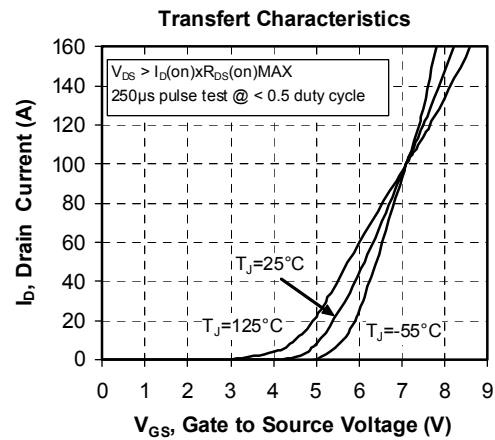
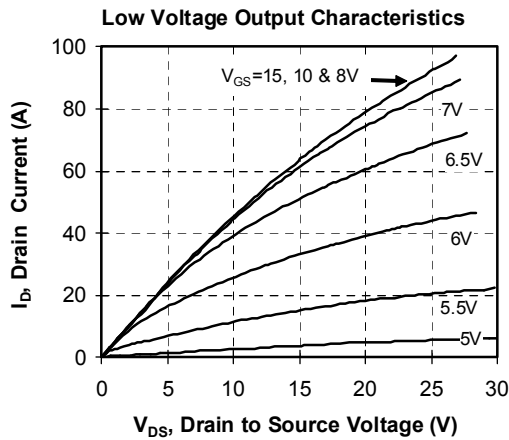
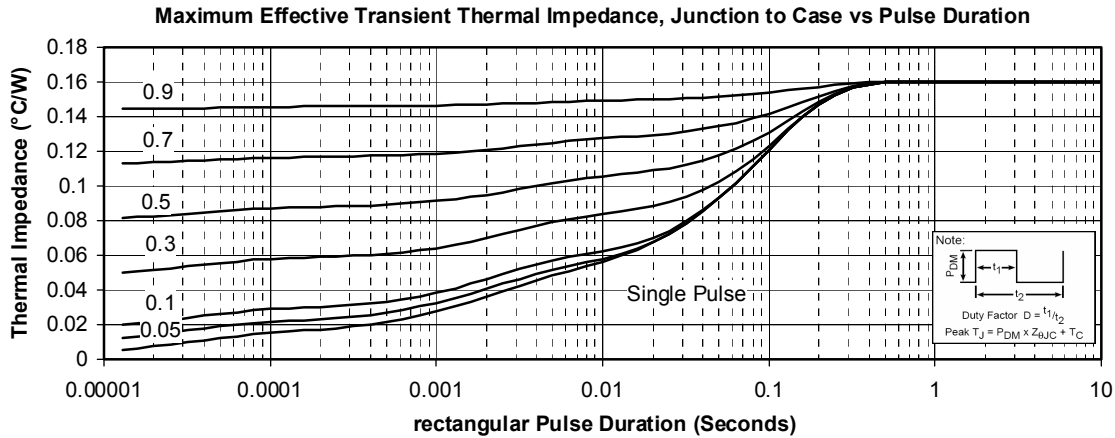
SP4 Package outline (dimensions in mm)

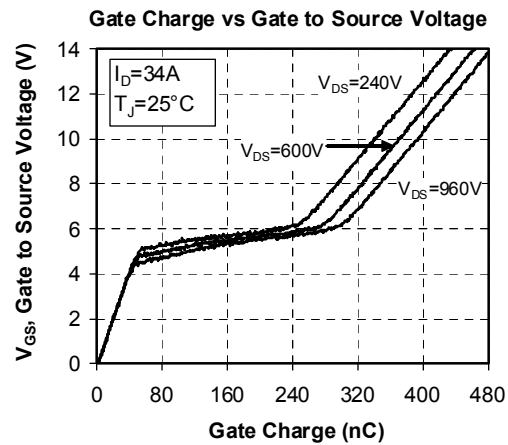
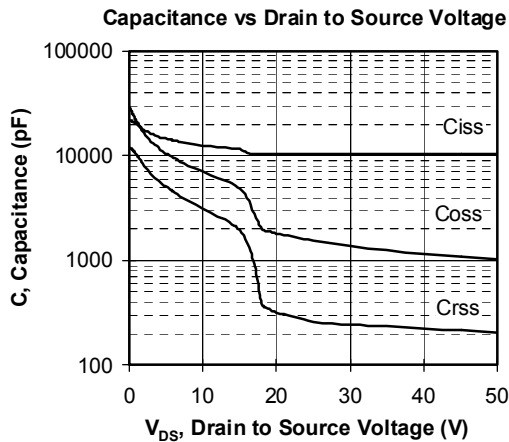
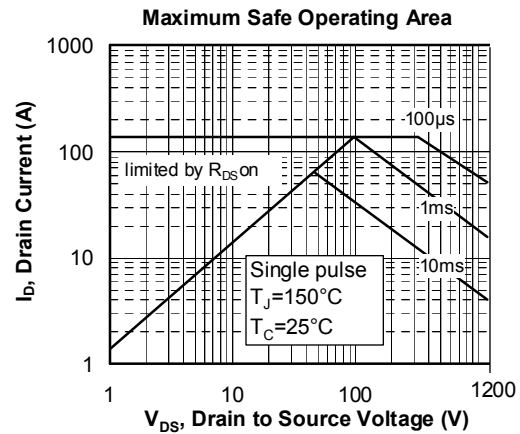
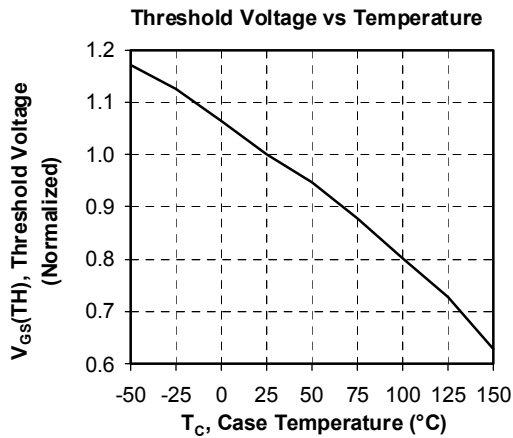
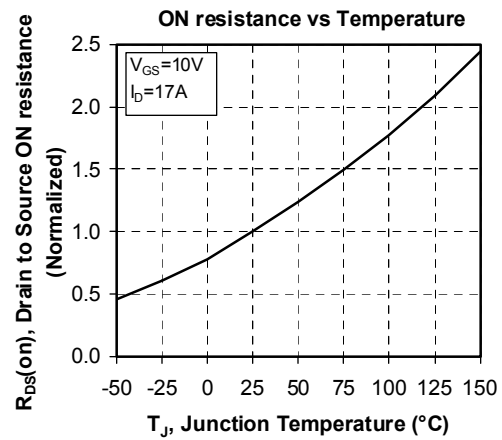
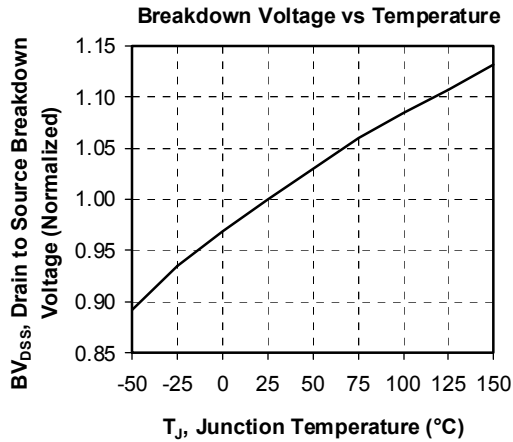


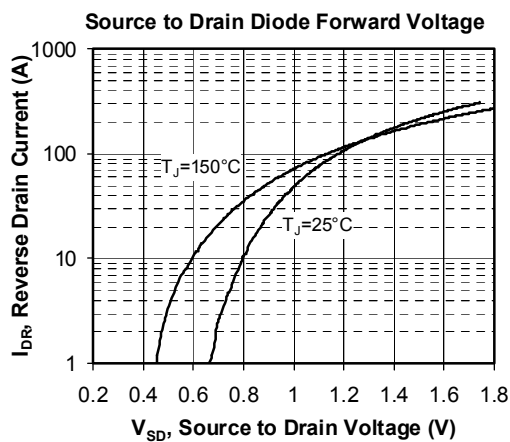
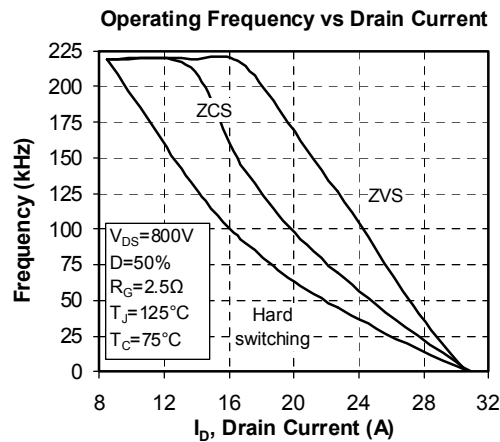
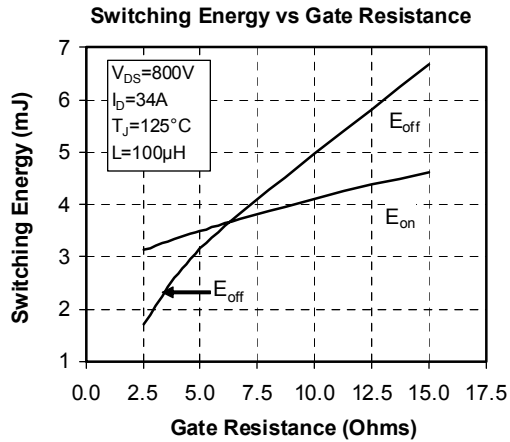
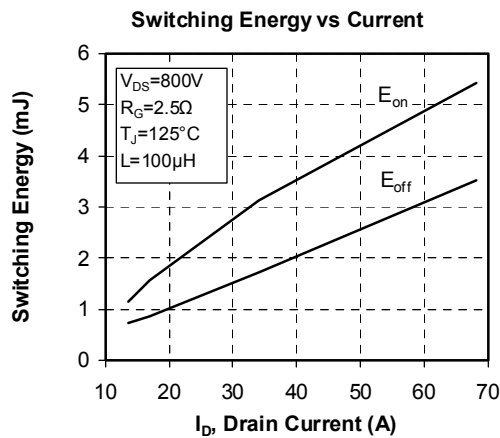
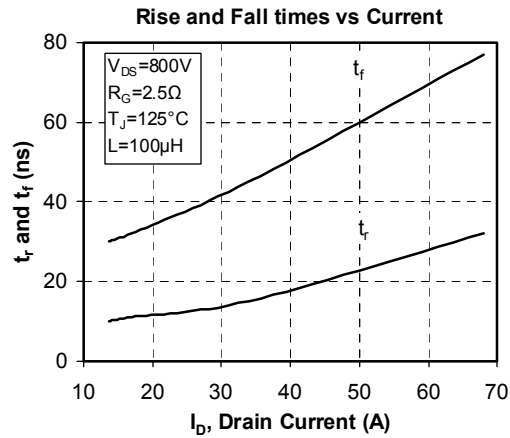
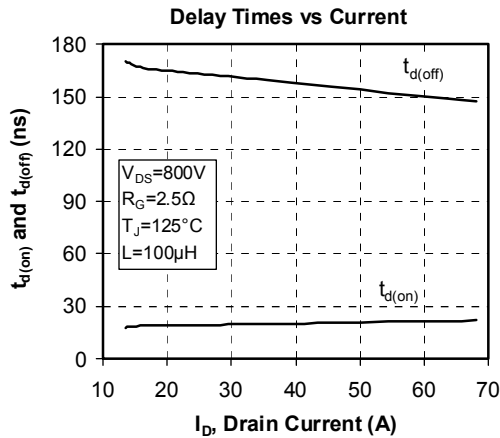
ALL DIMENSIONS MARKED "*" ARE TOLERENCED AS: ± 0.1

See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

Typical Performance Curve







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